MOSFET – Dual, N-Channel, Small Signal, SC-88

30 V, 250 mA

Features

- Low Gate Charge for Fast Switching
- Small Footprint 30% Smaller than TSOP–6
- ESD Protected Gate
- AEC Q101 Qualified NVTJD4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

MAXIMUM RATINGS (T_J = 25° C unless otherwise stated)

Param	Symbol	Value	Units			
Drain-to-Source Voltage	V _{DSS}	30	V			
Gate-to-Source Voltage	l		V _{GS}	±20	V	
Continuous Drain	Steady	$T_A = 25 \ ^\circ C$	I _D	250	mA	
Current (Note T)	Current (Note 1) State			180		
Power Dissipation (Note 1) Steady		T _A = 25 °C	P _D	272	mW	
Pulsed Drain Current	I _{DM}	600	mA			
Operating Junction and S	T _J , T _{STG}	–55 to 150	°C			
Source Current (Body Di	ا _S	250	mA			
Lead Temperature for So (1/8" from case for 10 s)	ΤL	260	°C			

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State	$R_{\theta JA}$	458	°C/W
Junction-to-Lead - Steady State	$R_{\theta JL}$	252	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

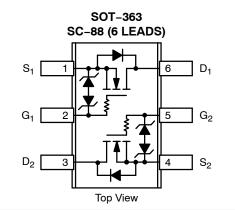
1. Surface mounted on FR4 board using min pad size (Cu area = 0.155 in sq [1 oz] including traces).

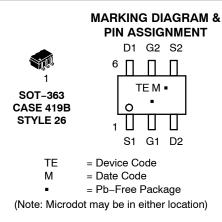


ON Semiconductor®

www.onsemi.com

V _{(BR)DSS} R _{DS(on)} TYP		I _D Max
30 V	1.0 Ω @ 4.0 V	250 mA
	1.5 Ω @ 2.5 V	230 MA





ORDERING INFORMATION

Device	Package	Shipping [†]
NTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NVTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

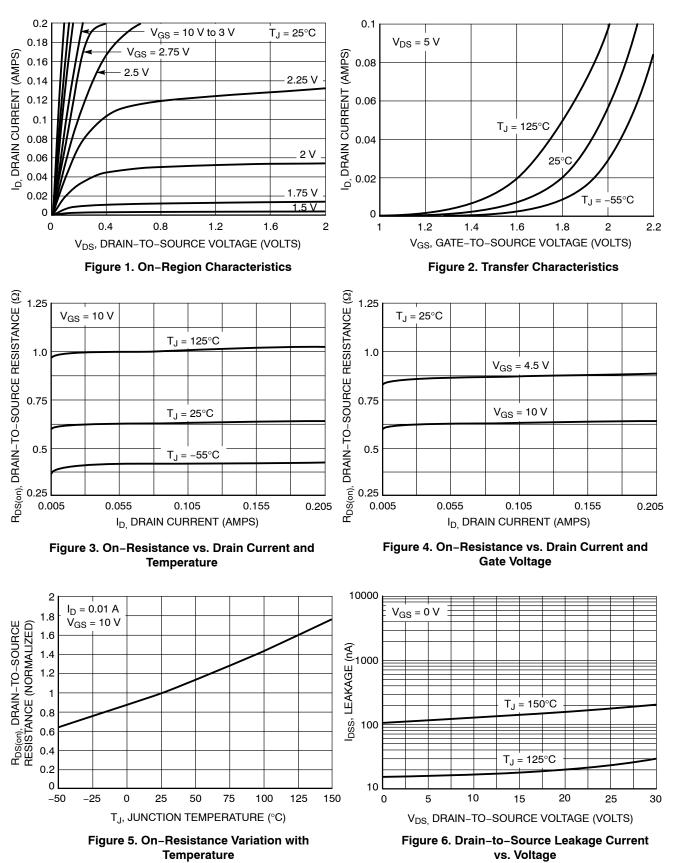
Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
OFF CHARACTERISTICS	· · · ·		·			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 100 μ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			56		mV/ °C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V, V_{DS} = 30 V$			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±10 V			±1.0	μΑ
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 100 \ \mu A$	0.8	1.2	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-3.2		mV/ °C
Drain-to-Source On Resistance	R _{DS(on)}	V_{GS} = 4.0 V, I _D = 10 mA		1.0	1.5	Ω
		V_{GS} = 2.5 V, I _D = 10 mA		1.5	2.5	-
Forward Transconductance	9 FS	$V_{DS} = 3.0 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$		80		mS
CHARGES AND CAPACITANCES				•	•	
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz,		20	33	pF
Output Capacitance	C _{OSS}	V _{DS} = 5.0 V		19	32	
Reverse Transfer Capacitance	C _{RSS}			7.25	12	
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = 5.0 \text{ V}, V_{DS} = 24 \text{ V},$		0.9	1.3	nC
Threshold Gate Charge	Q _{G(TH)}	I _D = 0.1 A		0.2		
Gate-to-Source Charge	Q _{GS}			0.3		
Gate-to-Drain Charge	Q _{GD}			0.2		
SWITCHING CHARACTERISTICS (No	ote 3)					
Turn-On Delay Time	td _(ON)	$V_{GS} = 4.5 V, V_{DD} = 5.0 V,$		17		ns
Rise Time	tr	I_D = 10 mA, R_G = 50 Ω		23		
Turn-Off Delay Time	td _(OFF)			94		
Fall Time	tf			82		
DRAIN-SOURCE DIODE CHARACTE	RISTICS		·	•	•	

Forward Diode Voltage	V _{SD}	$V_{GS} = 0 V$,	$T_J = 25^{\circ}C$	0.65	0.7	V
		l _S = 10 mA	T _J = 125°C	0.45		
Reverse Recovery Time	t _{RR}	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V, \ dI_S/dt = 8.0 \ A/\mu s, \\ I_S = 10 \ mA \end{array}$		12.4		ns

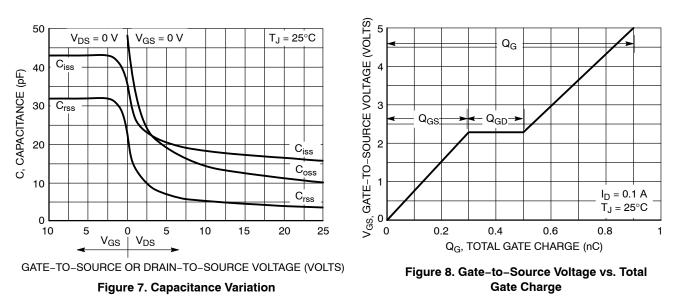
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%.

3. Switching characteristics are independent of operating junction temperatures.



TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

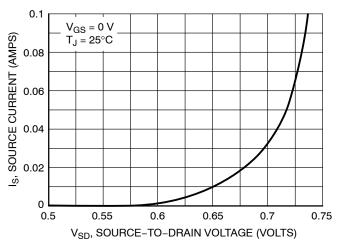
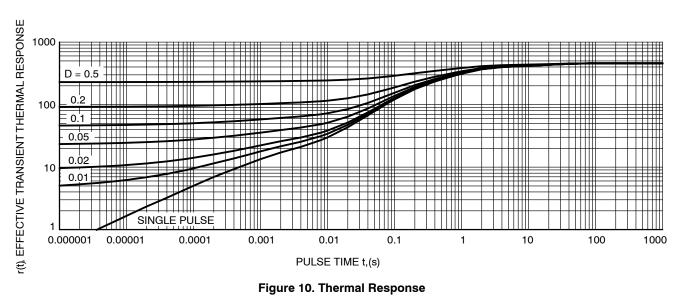


Figure 9. Diode Forward Voltage vs. Current

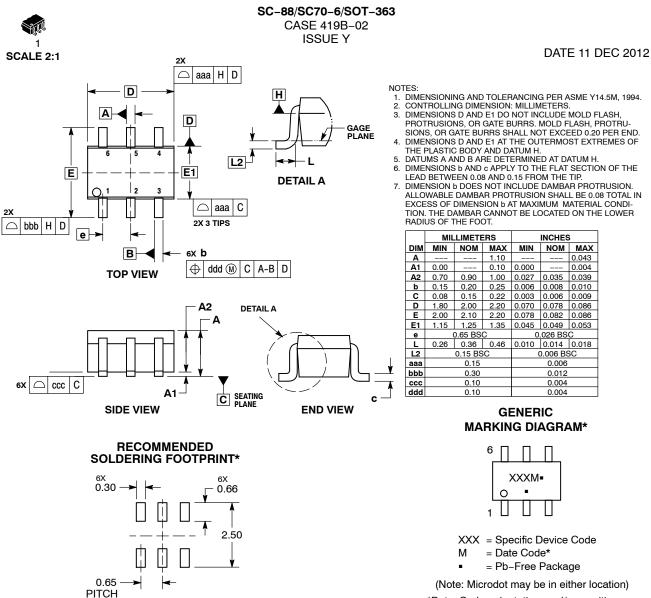


www.onsemi.com

0.043

0.004





DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

Electronic versions are uncontrolled except when accessed directly from the Document Repository. DOCUMENT NUMBER: 98ASB42985B Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SC-88/SC70-6/SOT-363 PAGE 1 OF 2 ON Semiconductor and unarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others

SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-88/SC70-6/SOT-363		PAGE 2 OF 2	
ON Semiconductor reserves the right the suitability of its products for any pa	to make changes without further notice to an articular purpose, nor does ON Semiconductor	stries, LLC dba ON Semiconductor or its subsidiaries in the United States y products herein. ON Semiconductor makes no warranty, representation r assume any liability arising out of the application or use of any product or cidental damages. ON Semiconductor does not convey any license under	or guarantee regarding circuit, and specifically	

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

٥